LISTING OF THE CLAIMS

This listing of claims replaces all prior versions.

1. (Previously presented) A semiconductor device having opposed first and second major surfaces, comprising:

a body region at the first major surface;

at least one cell having longitudinally spaced source and drain implantations extending into the body region from the first major surface, the source and drain implantations being spaced away from the substrate by part of the body region and defining a channel part of the body region between the source and drain implantations; and

at least one insulated gate trench extending longitudinally from the source implantation to the drain implantation through the body region, the insulated gate trench including a gate conductor insulated from the source and drain implantations and the body region by a gate dielectric along the side and end walls and the base of the trench, the source and drain implantations extending along part of the side walls of the trench,

wherein the source and drain implantations include conductive shallow contact regions at the first major surface extending vertically into the body to a depth of no more than 35% of the depth of the trench.

2. (Original) A semiconductor device according to claim 1 wherein the body region is of first conductivity type and the shallow contact regions are of a second conductivity type opposite to the first conductivity type.

3. (Previously presented) A semiconductor device according to claim 1 or 2 wherein each of the source and drain implantations further comprises a lower doped region of lower doping than the shallow contact region.

4. (Previously presented) A semiconductor device according to claim 3, wherein:

the source implantation includes a higher doped shallow source contact region and a lower doped source drift region between the higher doped source contact region and the body;

the drain implantation includes a higher doped shallow drain contact region and a lower doped drain drift region between the higher doped drain contact region and the body;

the insulated gate trench includes potential plate regions extending longitudinally on either side of a central region, the potential plate regions being adjacent to the source and drain drift regions respectively, and the central region being adjacent to the body; and

the thickness of the gate dielectric sidewalls of the insulated gate trench is greater in the potential plate regions of the insulated gate than the central region.

5. (Previously presented) A semiconductor device according to claim 1 comprising a plurality of cells laterally spaced across the first major surface.

6. (Previously presented) A semiconductor device according to claim 5 wherein gate trenches alternate with the plurality of cells laterally across the first major surface.

7. (Previously presented) A semiconductor device according to claim 5 wherein each cell has a gate trench laterally within the confines of the cell.

8. (Previously presented) A semiconductor device according to claim 3 wherein the lower doped region of lower doping than the shallow contact region extends vertically below the shallow contact region to a depth at least 80% of the depth of the trench.

9. (Previously presented) A semiconductor device according to claim 1, wherein the source and drain implantations consist exclusively of the shallow contact region.

10. (Previously presented) A semiconductor device according to claim 1 on a conductive substrate of first conductivity type.